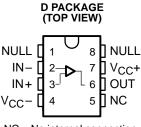
- Very High Speed
 - -270 MHz Bandwidth (Gain = 1, -3 dB)
 - 400 V/µsec Slew Rate
 - 40-ns Settling Time (0.1%)
- High Output Drive, I_O = 100 mA
- Excellent Video Performance
 - 60 MHz Bandwidth (0.1 dB, G = 1)
 - 0.04% Differential Gain
 - 0.15° Differential Phase
- Very Low Distortion
 - THD = -72 dBc at f = 1 MHz
- Wide Range of Power Supplies
 V_{CC} = ± 2.5 V to ± 15 V,
 I_{CC} = 7.5 mA
- Evaluation Module Available

description

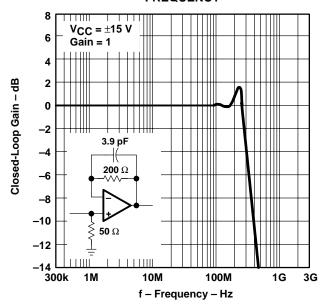
The THS4001 is a very high-performance, voltage-feedback operational amplifier especially suited for a wide range of video applications. The device is specified to operate over a wide range of supply voltages from \pm 15 V to \pm 2.5 V. With a bandwidth of 270 MHz, a slew rate of over 400 V/ μ s, and settling times of less than 30 ns, the THS4001 offers the unique combination of high performance in an easy to use voltage feedback configuration over a wide range of power supply voltages.

The THS4001 is stable at all gains for both inverting and noninverting configurations. It has a high output drive capability of 100 mA and draws



NC - No internal connection

CLOSED-LOOP GAIN vs FREQUENCY



only 7.5 mA of quiescent current. Excellent professional video results can be obtained with the differential gain/phase performance of $0.04\%/0.15^{\circ}$ and 0.1 dB gain flatness to 60 MHz. For applications requiring low distortion, the THS4001 is ideally suited with total harmonic distortion of -72 dBc at f = 1 MHz.

HIGH-SPEED AMPLIFIER FAMILY

DEVICE	DEVICE ARCH.			SUPPL OLTAC		BW (MHz)	SR	THD f = 1 MHz	t _S 0.1%	DIFF. GAIN	DIFF. PHASE	۷ _n
	VFB	CFB	5 V	±5 V	±15 V	(IVITIZ)	(V/ μ s)	(dB)	(ns)	GAIN	PHASE	(nV/√Hz)
THS3001		•		•	•	420	6500	-96	40	0.01%	0.02°	1.6
THS4001	•		•	•	•	270	400	-72	40	0.04%	0.15°	12.5
THS4031/32	•			•	•	100	100	-72	60	0.02%	0.03°	1.6
THS4061/62	•			•	•	180	400	-72	40	0.02%	0.02°	14.5



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

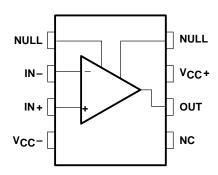


AVAILABLE OPTIONS

	PACKAGED DEVICES							
TA	SMALL OUTLINE [†] (D)	EVALUATION MODULE						
0°C to 70°C	THS4001CD	THS4001EVM						
−40°C to 85°C	THS4001ID	_						

[†]The D packages are available taped and reeled. Add an R suffix to the device type (i.e., THS4001CDR).

symbol



absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, V _{CC} to V _{CC+}	
Input voltage, V _I	±V _{CC}
Output current, IO	
Differential input voltage, V _{ID}	
Continuous total power dissipation	. See Dissipation Ratings Table
Operating free air temperature, T _A :C suffix	0°C to 70 °C
I suffix	–40°C to 85 °C
Storage temperature, T _{stq}	–65°C to 150 °C
Lead temperature 1,6 mm (1/16 lnch) from case for 10 seconds	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{$\mbox{Λ}}} \leq 25^{\circ}\mbox{$\mbox{$\mbox{C}$}}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
D	740 mW	6 mW/°C	475 mW	385 mW



CAUTION: The THS4001 provides ESD protection circuitry. However, permanent damage can still occur if this device is subjected to high-energy electrostatic discharges. Proper ESD precautions are recommended to avoid any performance degradation or loss of functionality



recommended operating conditions

		MIN	TYP	MAX	UNIT
Supply voltage Vale	Dual supply	±2.5		±16	V
Supply voltage, V _{CC}	Single supply	5		32	٧
Quiggoont gurrent le e	±15 V		7.8	9.5	mΑ
Quiescent current, ICC	±5 V, ±2.5 V		6.7	8	IIIA
Operating free cir temperature T.	C suffix	0		70	°C
Operating free-air temperature, T _A	I suffix	-40		85	C

electrical characteristics, V_{CC} = ± 15 V, R_L = 150 Ω , T_A = 25°C (unless otherwise noted)

	PARAMETER	TEST C	ONDITIONS	VCC	MIN	TYP	MAX	UNIT
	Differential ania arman			±15 V		0.04%		
	Differential gain error	Gain = 2,	$R_L = 150 \Omega$,	±5 V		0.01%		
	Differential phase area	f = 3.58 MHz	_	±15 V		0.15°		
	Differential phase error			±5 V		0.08°		
\/.a	Input offset voltage	T _A = 25°C		±15 V,		2	8	mV
VIO	input onset voitage	T _A = full range		±5 V			10	IIIV
lin	Input bias current	T _A = 25°C		±15 V, ±5 V		2.6	5	μΑ
lВ	input bias current	T _A = full range	T _A = full range				6	μΑ
	Large to afficient assumption	T _A = 25°C	±15 V,		35	200	· nA	
los	Input offset current	T _A = full range	±5 V			500		
		$V_{O} = \pm 10 \text{ V},$	T _A = 25°C		5	10		
		$R_L = 1 k\Omega$	T _A = full range	±15 V	3			\//==\/
	Open-loop gain	$V_0 = \pm 2.5 \text{ V},$	T _A = 25°C	.5./	3	6		V/mV
		$R_L = 500 \Omega$	T _A = full range	±5 V	2			
01.100			T _A = 25°C		85	100		
CMRR	Common-mode rejection ratio	$V(CM) = \pm 12 V$	T _A = full range	±15 V	75			dB
DODE		T _A = 25°C	•	±15 V,	75	85		
PSRR	Power supply rejection ratio	T _A = full range		±5 V	70			dB
					13.5	14.8		V
				±15 V	to	to		
VICR	Common-mode input voltage range				-13	-14		
				±5 V	3.6 to	4.4 to		
					-2.7	-3.6		
				±15 V	±13	±13.5		
٧o	Output voltage swing	$R_L = 500 \Omega$		±5 V	±3.3	±3.8		V
				±2.5 V	±0.8	±1.3		
				±15 V	50	100		
lo	Output current	Gain =+ 2,	Gain =+ 2, $R_L = 20 \Omega$		50	100		mA
				±2.5 V	50	100		
THD	Total harmonic distortion	V _I = 1 V _(PP) ,	f = 1 MHz	±15 V		-72		dBc
R _I	Input resistance	· /				10		МΩ
Cl	Input capacitance					1.5		pF
RO	Output resistance	Open loop				10		Ω

THS4001 270-MHz HIGH-SPEED AMPLIFIER

SLOS206A- DECEMBER 1997 - REVISED MARCH 1999

operating characteristics, V_{CC} = ± 15 V, R_L = 150 Ω , T_A = 25°C (unless otherwise noted)

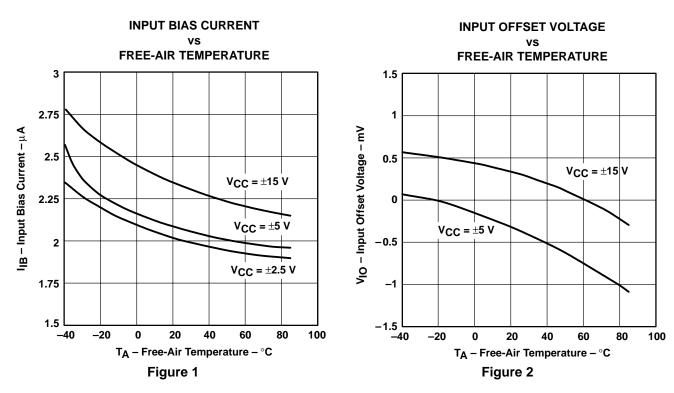
	PARAMETER	TEST COND	ITIONS	VCC	MIN	TYP	MAX	UNIT
				±15 V		400		
	Slew rate	Gain = -1				400		V/μs
				±2.5 V		350		
	Settling time to 0.1%	10 V step (0 to 10 V),	Gain = -1	±15 V		40		ns
	Setting time to 0.1 %	-2.5 V to 2.5 V step,	±5 V		30		115	
				±15 V		270		
		Gain = +1, $R_f = 150 \Omega$	$R_L = 150 \Omega$,	±5 V		220		MHz
	−3 dB Bandwidth	111 - 100 22		±2.5 V		180		
	-3 dB Baridwidtri			±15 V		80		MHz
		Gain = -1 , R _f = 150 Ω	$R_L = 150 \Omega$,	±5 V		75		
		11(1 = 100 22	±2.5 V		70			
				±15 V		60		
	Bandwidth for 0.1 dB flatness	Gain = +1	±5 V		50		MHz	
				±2.5 V		40		
Vn	Equivalent input noise voltage	f = 10 kHz		±15 V, ±5 V		12.5		nV/√ Hz
In	Equivalent input noise current	f = 10 kHz		±15 V, ±5 V		1.5		pA/√ Hz

TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
l _{IB}	Input bias current	vs Free-air temperature	1
VIO	Input offset voltage	vs Free-air temperature	2
	Open-loop gain	vs Frequency	3
	Phase	vs Frequency	3
	Differential gain	vs DC voltage	4, 5
	Differential phase	vs DC voltage	4, 5
	Closed-loop gain	vs Frequency	6, 7
CMRR	Common-mode rejection ratio	vs Frequency	8
PSRR	Dower cumby rejection ratio	vs Frequency	9
PSKK	Power-supply rejection ratio	vs Free-air temperature	10
V- ()	Output valtage output	vs Supply voltage	11
VO(PP)	Output voltage swing	vs Load resistance	12
	Bandwidth (-3 dB)	vs Feedback resistance	13, 14
la a	Cumply august	vs Supply voltage	15
ICC	Supply current	vs Free-air temperature	16
Env	Noise spectral density	vs Frequency	17
THD	Total harmonic distortion	vs Frequency	18





OPEN-LOOP GAIN AND PHASE

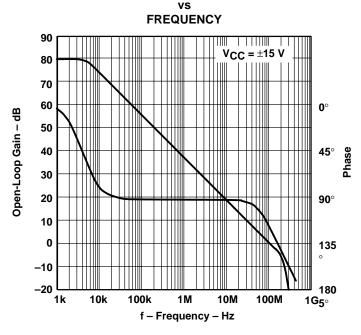


Figure 3

DIFFERENTIAL GAIN AND DIFFERENTIAL PHASE

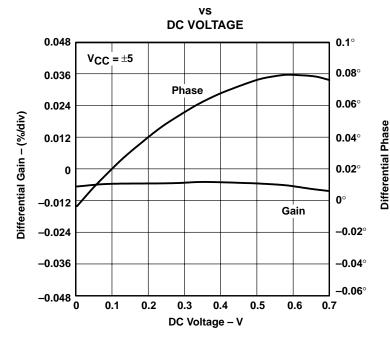


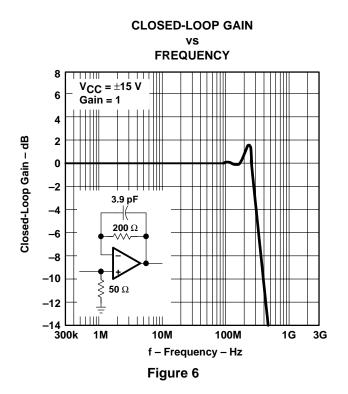
Figure 4

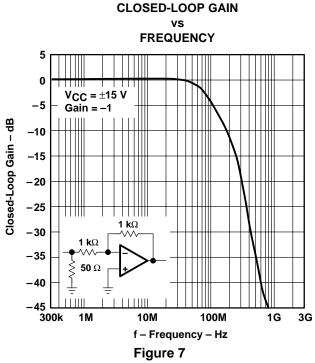
DIFFERENTIAL GAIN AND DIFFERENTIAL PHASE

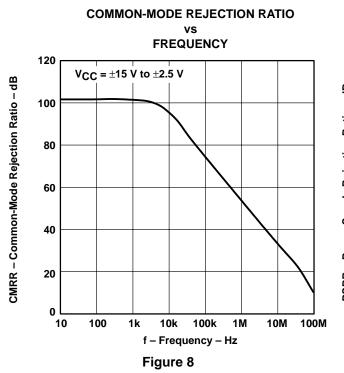
vs **DC VOLTAGE** 0.048 0.12° Phase $V_{CC} = \pm 15$ 0.1° 0.036 0.08° 0.024 Differential Gain – (%div) 0.06° 0.012 Gain 0.04° 0 -0.012 $\textbf{0.02}^{\circ}$ **0**° -0.024-0.036 -0.02° **-0.04**° -0.048-0.06 L -0.06° 0.1 0.2 0.3 0.4 0.5 0.6 0.7 DC Voltage - V

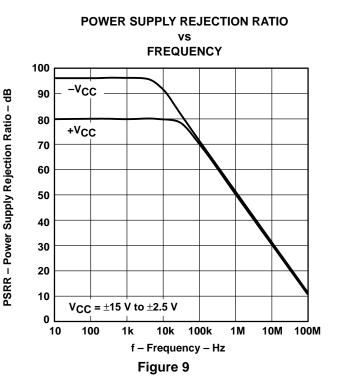
Figure 5

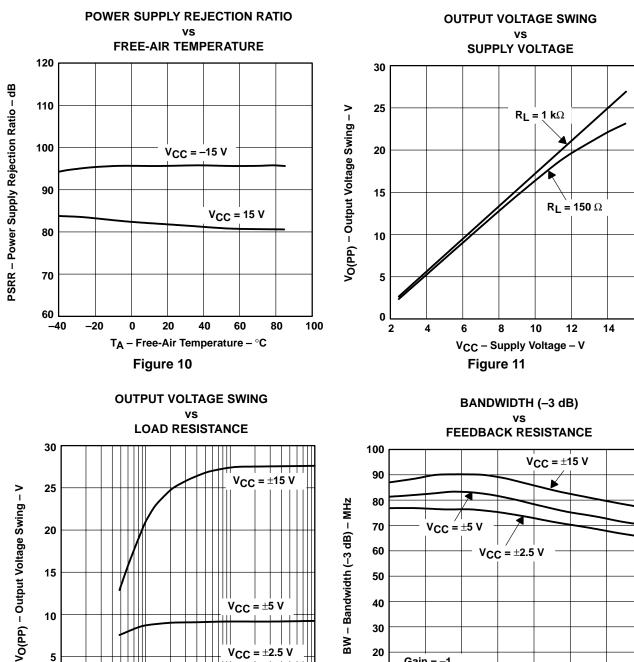


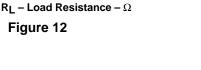




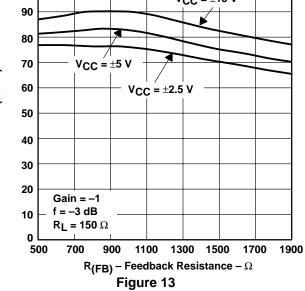








 $V_{CC} = \pm 2.5 V$

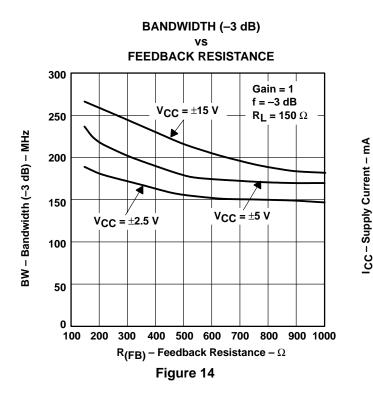


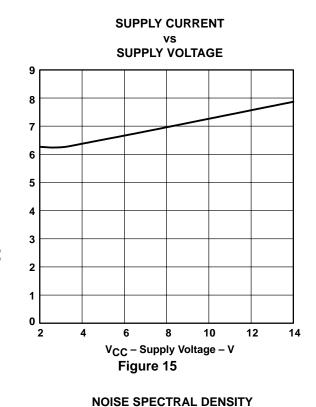
16

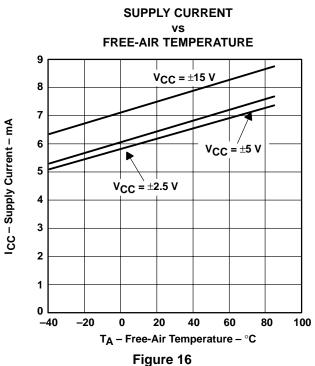
10000

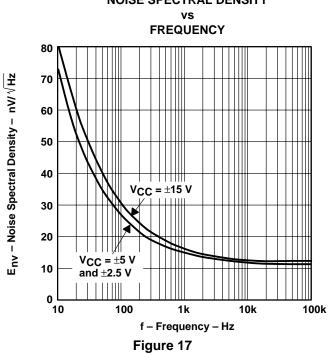
5

0 10

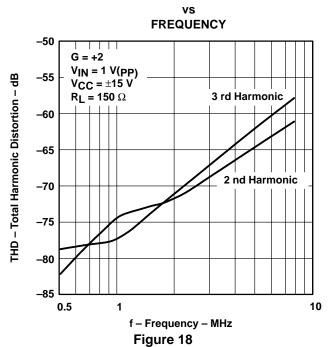








TOTAL HARMONIC DISTORTION



theory of operation

The THS4001 is a high speed, operational amplifier configured in a voltage feedback architecture. It is built using a 30-V, dielectrically isolated, complementary bipolar process with NPN and PNP transistors possessing f_{TS} of several GHz. This results in an exceptionally high performance amplifier that has a wide bandwidth, high slew rate, fast settling time, and low distortion. A simplified schematic is shown in Figure 19.

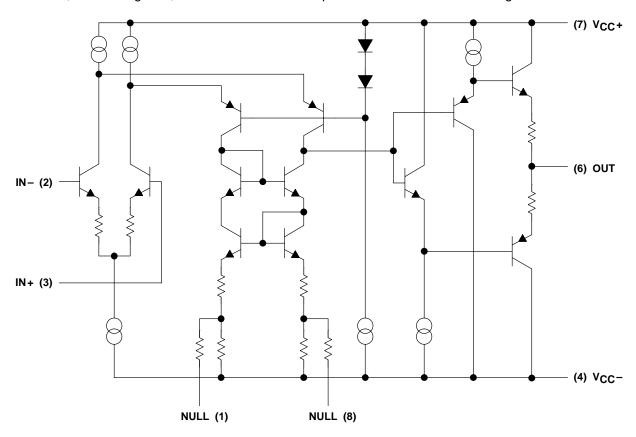


Figure 19. THS4001 Simplified Schematic

offset nulling

The THS4001 has very low input offset voltage for a high-speed amplifier. However, if additional correction is required, an offset nulling function has been provided. By placing a potentiometer between terminals 1 and 8 of the device and tying the wiper to the negative supply, the input offset can be adjusted. This is shown in Figure 20.

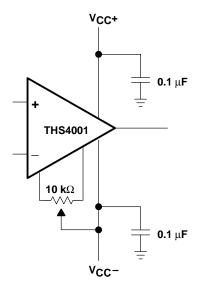


Figure 20. Offset Nulling Schematic

optimizing unity gain response

Internal frequency compensation of the THS4001 was selected to provide very wideband performance yet still maintain stability when operated in a noninverting unity gain configuration. When amplifiers are compensated in this manner there is usually peaking in the closed loop response and some ringing in the step response for very fast input edges, depending upon the application. This is because a minimum phase margin is maintained for the G=+1 configuration. For optimum settling time and minimum ringing, a feedback resistor of $200\,\Omega$ should be used as shown in Figure 21. Additional capacitance can also be used in parallel with the feedback resistance if even finer optimization is required.

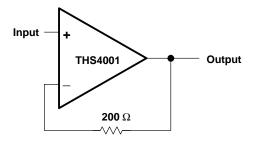


Figure 21. Noninverting, Unity Gain Schematic



driving a capacitive load

Driving capacitive loads with high performance amplifiers is not a problem as long as certain precautions are taken. The first is to realize that the THS4001 has been internally compensated to maximize its bandwidth and slew rate performance. When the amplifier is compensated in this manner, capacitive loading directly on the output will decrease the device's phase margin leading to high frequency ringing or oscillations. Therefore, for capacitive loads of greater than 10 pF, it is recommended that a resistor be placed in series with the output of the amplifier, as shown in Figure 22. A minimum value of 20 Ω should work well for most applications. For example, in 75- Ω transmission systems, setting the series resistor value to 75 Ω both isolates any capacitance loading and provides the proper line impedance matching at the source end.

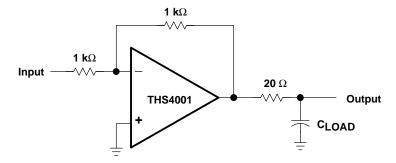


Figure 22. Driving a Capacitive Load

circuit layout considerations

In order to achieve the levels of high frequency performance of the THS4001, it is essential that proper printed-circuit board high frequency design techniques be followed. A general set of guidelines is given below. In addition, a THS4001 evaluation board is available to use as a guide for layout or for evaluating the device performance.

- Ground planes It is highly recommended that a ground plane be used on the board to provide all
 components with a low inductive ground connection. However, in the areas of the amplifier inputs and
 output, the ground plane can be removed to minimize the stray capacitance.
- Proper power supply decoupling Use a 6.8-μF tantalum capacitor in parallel with a 0.1-μF ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1-μF ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1-μF capacitor should be placed as close as possible to the supply terminal. As this distance increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inches between the device power terminals and the ceramic capacitors.
- Sockets Sockets are not recommended for high speed op amps. The additional lead inductance in the socket pins will often lead to stability problems. Surface-mount packages soldered directly to the printed-circuit board is the best implementation.
- Short trace runs/compact part placements Optimum high frequency performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This will help to minimize stray capacitance at the input of the amplifier.



circuit layout considerations (continued)

Surface-mount passive components – Using surface mount passive components is recommended for high
frequency amplifier circuits for several reasons. First, because of the extremely low lead inductance of
surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small
size of surface-mount components naturally leads to a more compact layout thereby minimizing both stray
inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be
kept as short as possible.

evaluation board

An evaluation board is available for the THS4001 (literature number SLOP119). This board has been configured for very low parasitic capacitance in order to realize the full performance of the amplifier. A schematic of the evaluation board is shown in Figure 23. The circuitry has been designed so that the amplifier may be used in either an inverting or noninverting configuration. To order the evaluation board contact your local TI sales office or distributor. For more detailed information, refer to the *THS4001 EVM User's Manual* (literature number SLOU017).

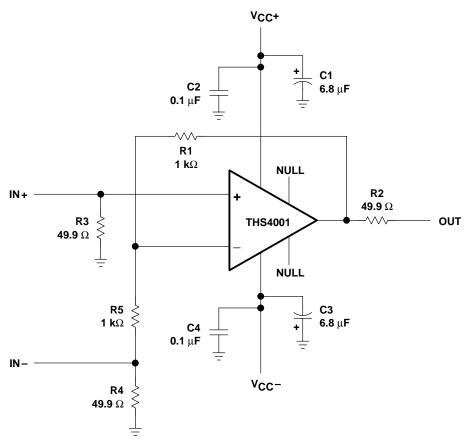


Figure 23.







10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
THS4001CD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		4001C	Samples
THS4001CDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	4001C	Samples
THS4001ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		40011	Samples
THS4001IDG4	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	40011	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	<u> </u>
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS4001CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

www.ti.com 26-Feb-2019



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS4001CDR	SOIC	D	8	2500	350.0	350.0	43.0



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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